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Team Nexperia

PHP36N03LT

N-channel TrenchMOS logic level FET

Rev. 04 — 8 July 2010

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Simple gate drive required due to low gate charge
- Suitable for logic level gate drive sources

1.3 Applications

- DC-to-DC convertors
- Switched-mode power supplies

1.4 Quick reference data

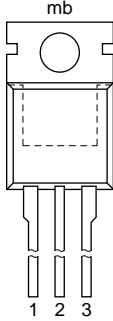
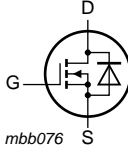
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	-	30	V
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1 ; see Figure 3	-	-	43.4	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	-	57.6	W
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; see Figure 9 ; see Figure 10	-	14	17	m Ω
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}$; $I_D = 36\text{ A}$; $V_{DS} = 15\text{ V}$; $T_j = 25\text{ °C}$; see Figure 11 ; see Figure 12	-	2.9	-	nC



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source ^[1]		
mb	D	mounting base; connected to drain		

SOT78 (TO-220AB)

[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3. Ordering information

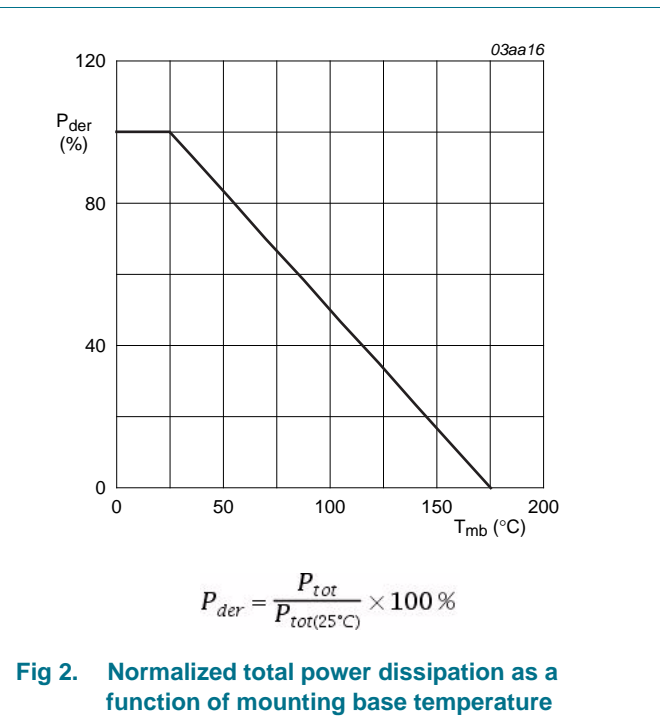
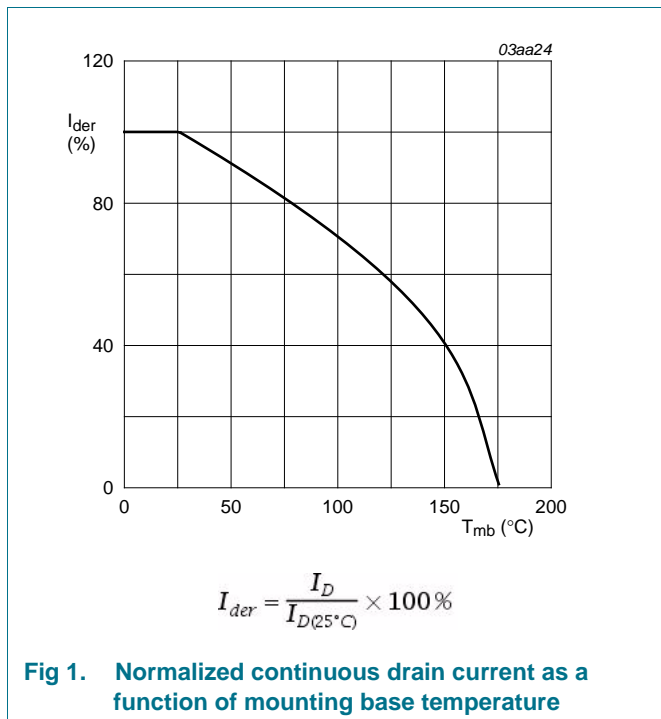
Type number	Package		
	Name	Description	Version
PHP36N03LT	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	30	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	30	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see Figure 1	-	30.7	A
		V _{GS} = 10 V; T _{mb} = 25 °C; see Figure 1 ; see Figure 3	-	43.4	A
I _{DM}	peak drain current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; see Figure 3	-	173.6	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2	-	57.6	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
Source-drain diode					
I _S	source current	T _{mb} = 25 °C	-	43.4	A
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C	-	173.6	A



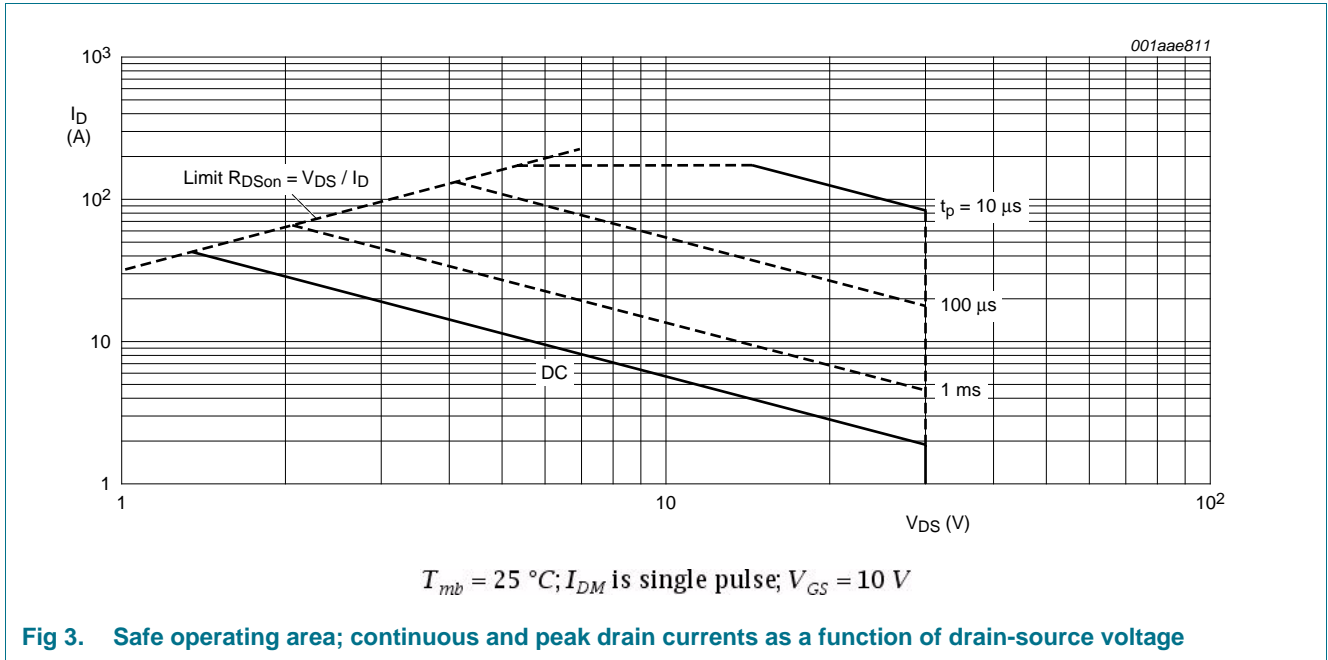


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	2.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W

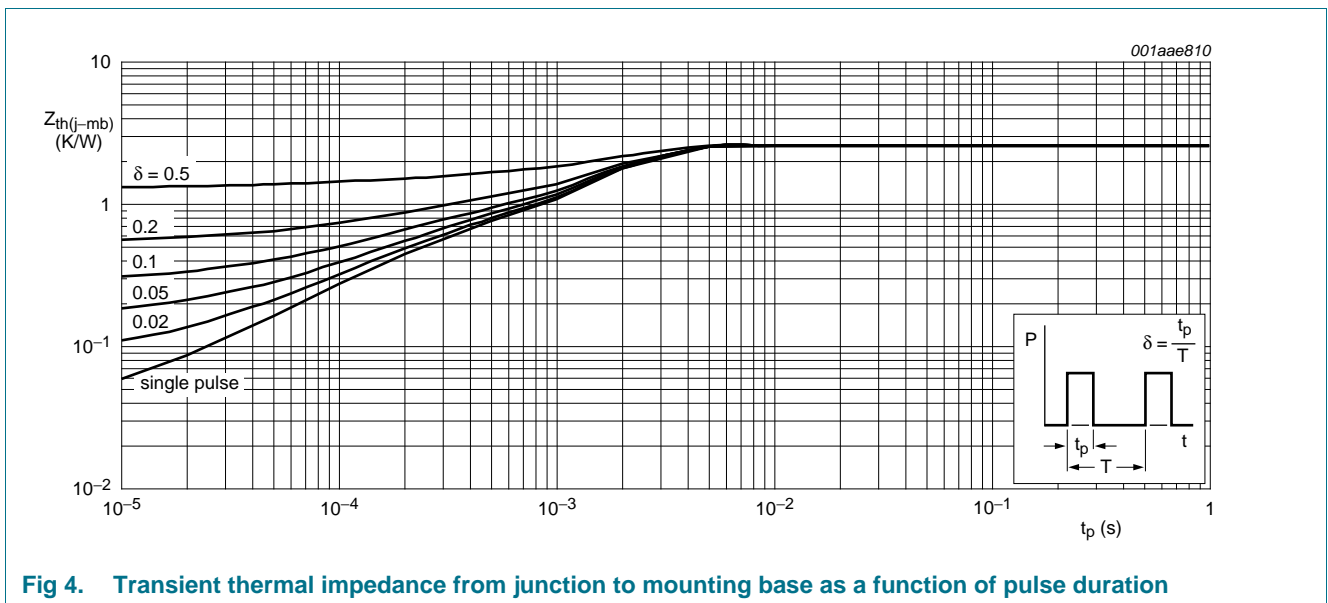
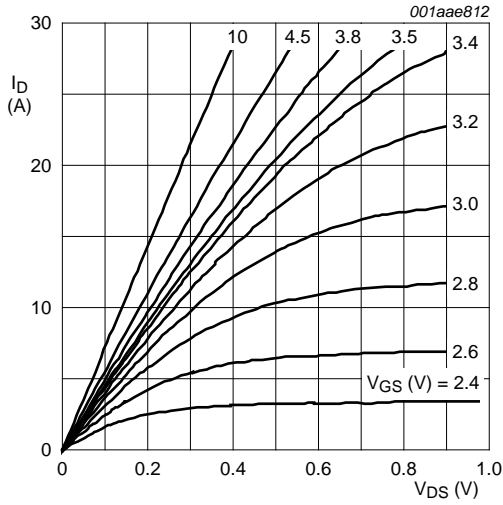


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

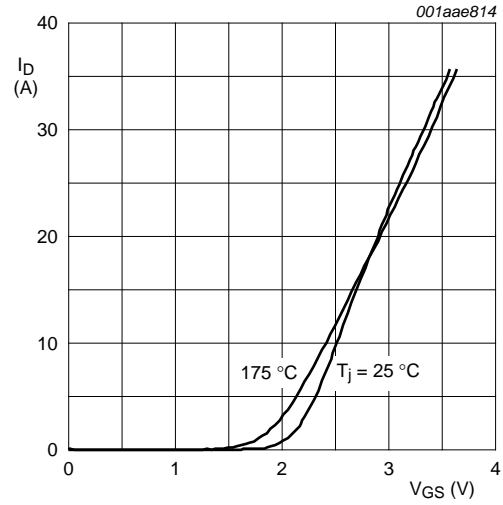
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ\text{C}$	27	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ\text{C}$	30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 7 ; see Figure 8	0.5	-	-	V
		$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 7 ; see Figure 8	1	1.5	2	V
		$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see Figure 7 ; see Figure 8	-	-	2.2	V
I_{DSS}	drain leakage current	$V_{DS} = 24 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ\text{C}$	-	0.05	1	μA
		$V_{DS} = 24 V; V_{GS} = 0 V; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ\text{C}$	-	10	100	nA
		$V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ\text{C}$	-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 25 A; T_j = 25 \text{ }^\circ\text{C};$ see Figure 9 ; see Figure 10	-	14	17	m Ω
		$V_{GS} = 4.5 V; I_D = 12 A; T_j = 175 \text{ }^\circ\text{C};$ see Figure 9 ; see Figure 10	-	32.4	39.6	m Ω
		$V_{GS} = 3.5 V; I_D = 5.2 A; T_j = 25 \text{ }^\circ\text{C};$ see Figure 9 ; see Figure 10	-	22	40	m Ω
		$V_{GS} = 4.5 V; I_D = 12 A; T_j = 25 \text{ }^\circ\text{C};$ see Figure 9 ; see Figure 10	-	18	22	m Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 36 A; V_{DS} = 15 V; V_{GS} = 10 V;$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 11 ; see Figure 12	-	18.5	-	nC
Q_{GS}	gate-source charge		-	4.2	-	nC
Q_{GD}	gate-drain charge		-	2.9	-	nC
C_{iss}	input capacitance	$V_{DS} = 25 V; V_{GS} = 0 V; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 13	-	690	-	pF
C_{oss}	output capacitance	$V_{DS} = 0 V; V_{GS} = 0 V; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 13	-	160	-	pF
C_{rss}	reverse transfer capacitance	$V_{DS} = 25 V; V_{GS} = 0 V; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 13	-	110	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15 V; R_L = 0.6 \Omega; V_{GS} = 10 V;$ $R_{G(ext)} = 10 \Omega; T_j = 25 \text{ }^\circ\text{C}$	-	6	-	ns
t_r	rise time		-	10	-	ns
$t_{d(off)}$	turn-off delay time		-	33	-	ns
t_f	fall time		-	19	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25 A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ\text{C};$ see Figure 14	-	0.97	1.2	V



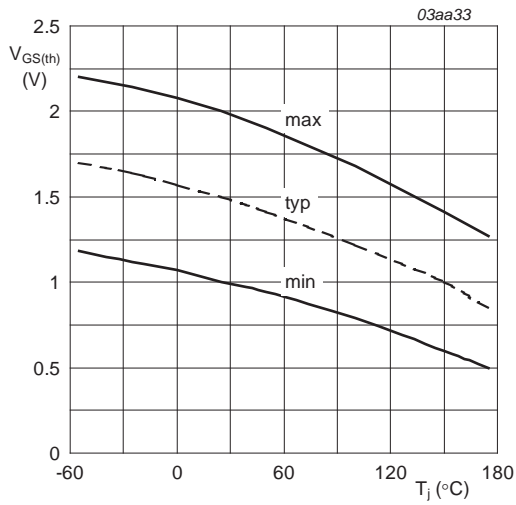
$T_j = 25\text{ }^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



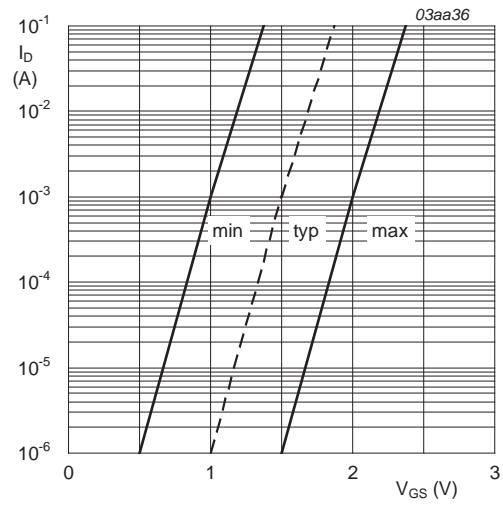
$V_{DS} > I_D \times R_{DS(on)}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

Fig 7. Gate-source threshold voltage as a function of junction temperature



$T_j = 25\text{ }^\circ\text{C}; V_{DS} = V_{GS}$

Fig 8. Sub-threshold drain current as a function of gate-source voltage

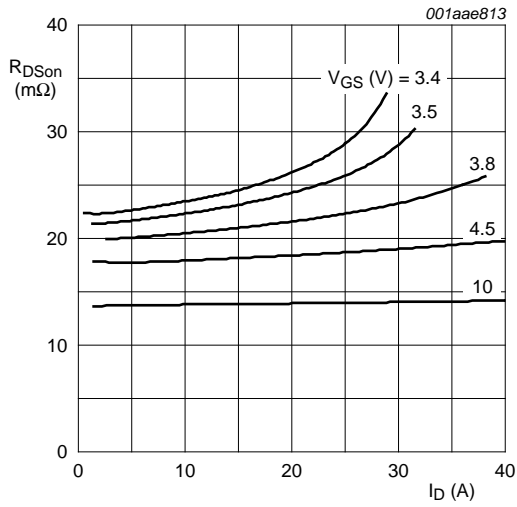
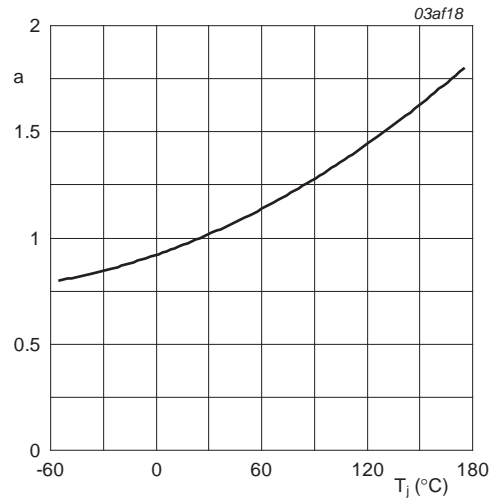
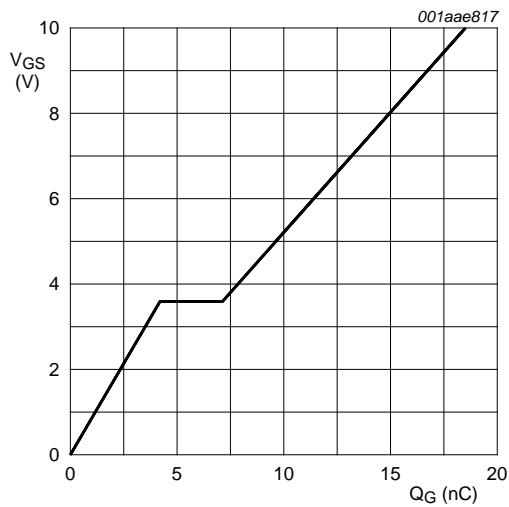


Fig 9. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature



$I_D = 36\text{ A}; V_{DS} = 15\text{ V}$

Fig 11. Gate-source voltage as a function of gate charge; typical values

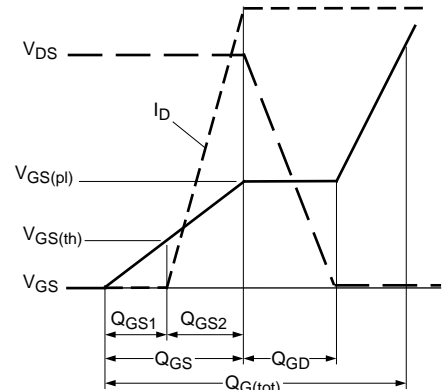
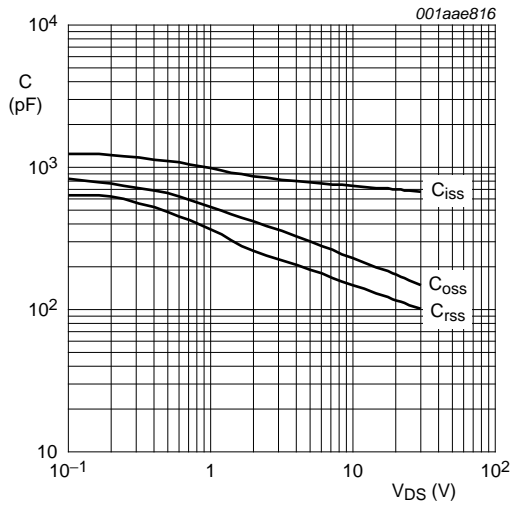
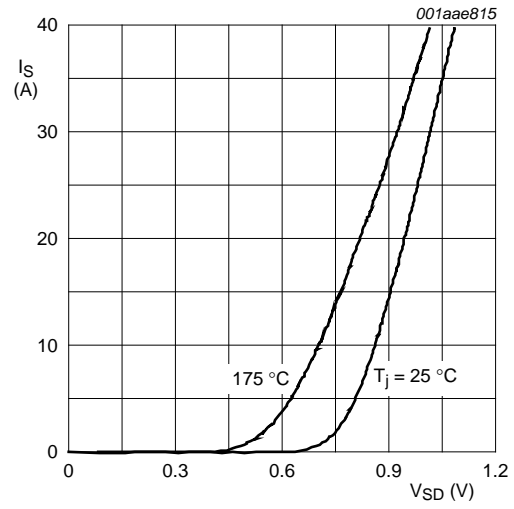


Fig 12. Gate charge waveform definitions



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0\text{ V}$

Fig 14. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

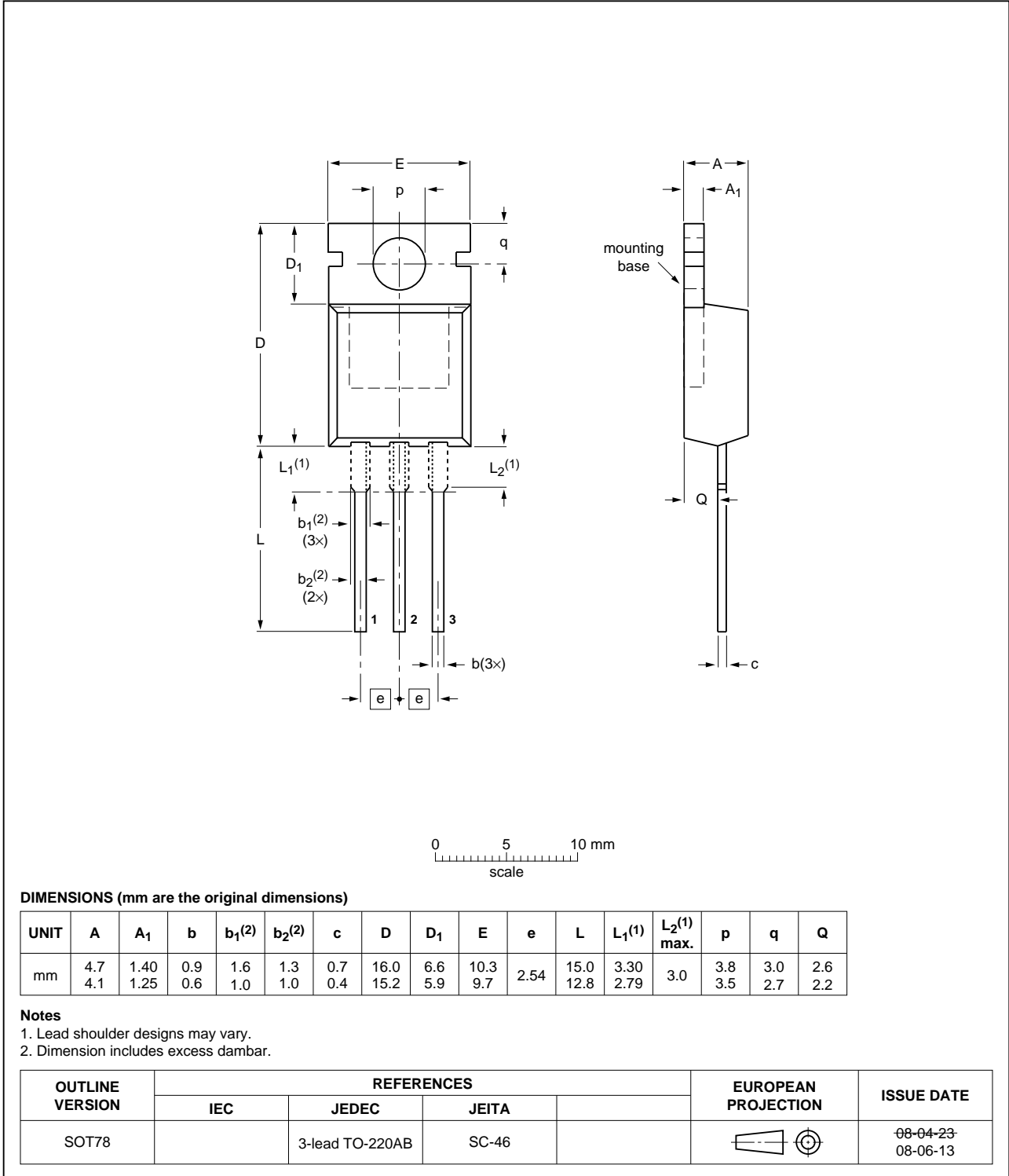


Fig 15. Package outline SOT78 (TO-220AB)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHP36N03LT v.4	20100708	Product data sheet	-	PHP36N03LT v.3
Modifications:	• Various changes to content.			
PHP36N03LT v.3	20100329	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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